



No.1224



2SD1398

NPN Triple Diffused Planar Type Silicon Transistor
For Horizontal Output (Built-in Damper Diode)

勝特力材料 886-3-5753170
勝特力电子(上海) 86-21-34970699
勝特力电子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)

Features:

- High Breakdown Voltage and High Reliability.
- High Switching Speed.
- Capable of being mounted easily due to one-point fixing type plastic mold package.

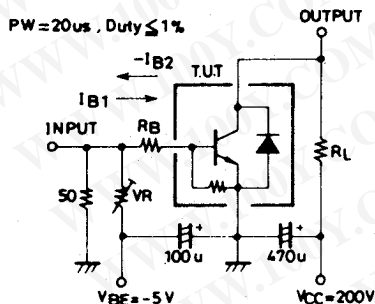
Absolute Maximum Ratings at Ta=25°C

			unit
Collector to Base Voltage	V _{CB0}	1500	V
Collector to Emitter Voltage	V _{CE0}	800	V
Emitter to Base Voltage	V _{EB0}	7	V
Collector Current	I _C	5	A
Peak Collector Current	i _{cp}	16	A
Collector Dissipation	P _C T _c =25°C	50	W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

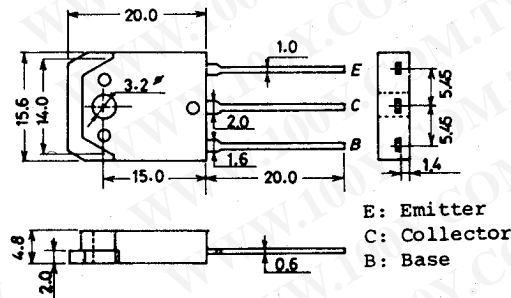
Electrical Characteristics at Ta=25°C

			min	typ	max	unit
Collector Cutoff Current	I _{CB0}	V _{CB} =800V, I _E =0			10	uA
Emitter Cutoff Current	I _{EB0}	V _{EB} =4V, I _C =0	40		130	mA
DC Current Gain	h _{FE}	V _{CE} =5V, I _C =1A	8			
Gain Bandwidth Product	f _T	V _{CE} =10V, I _C =1A		3		MHz
C-E Saturation Voltage	V _{CE(sat)}	I _C =4A, I _B =0.8A			5	V
B-E Saturation Voltage	V _{BE(sat)}	I _C =4A, I _B =0.8A			1.5	V
C-B Breakdown Voltage	V(BR) _{CBO}	I _C =5mA, I _E =0	1500			V
C-E Breakdown Voltage	V(BR) _{CEO}	I _C =100mA, R _{BE} =∞	800			V
E-B Breakdown Voltage	V(BR) _{EBO}	I _E =200mA, I _C =0	7			V
Diode Forward Voltage	V _F	I _{EC} =5A			2	V
Fall Time	t _f	I _C =4A, I _{B1} =0.8A, I _{B2} =-1.6A V _{CC} =200V, R _L =50ohm			0.7	us

Switching Time Test Circuit



Case Outline 2022 (unit:mm)



These specifications are subject to change without notice.